

FS2ASH-3

HIGH-SPEED SWITCHING USE

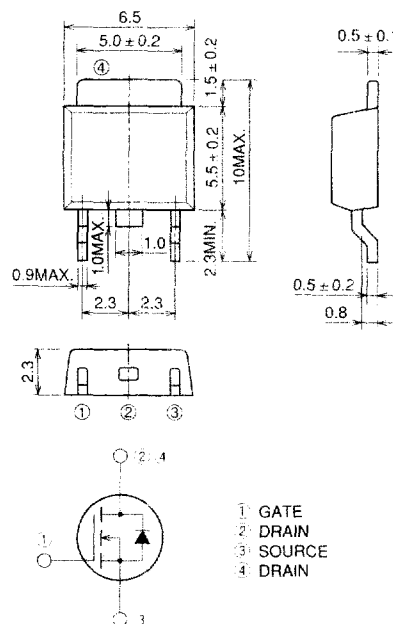
FS2ASH-3



- 2.5V DRIVE
- V_{DS} 150V
- $r_{DS(ON)}$ (MAX) 0.75Ω
- I_D 2A
- Integrated Fast Recovery Diode (TYP.) 65ns

OUTLINE DRAWING

Dimensions in mm



MP-3

APPLICATION

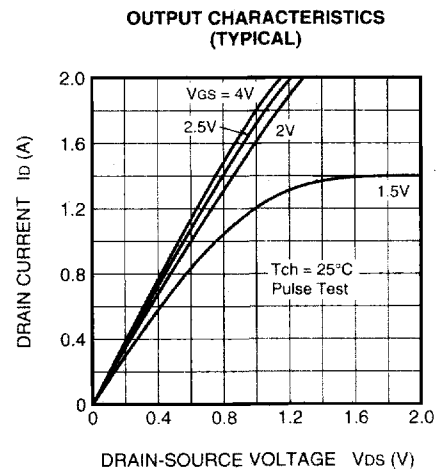
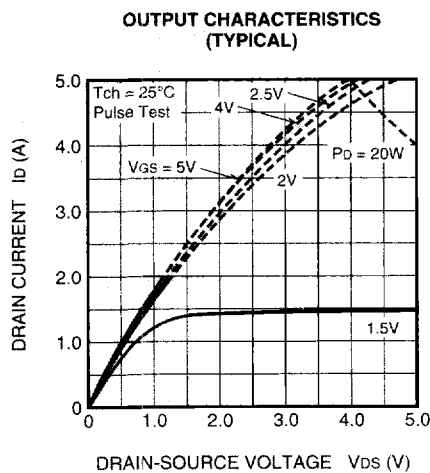
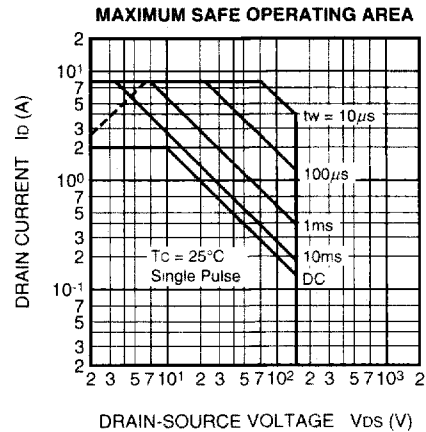
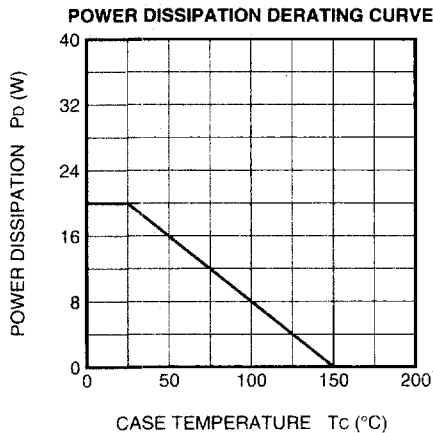
Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$)

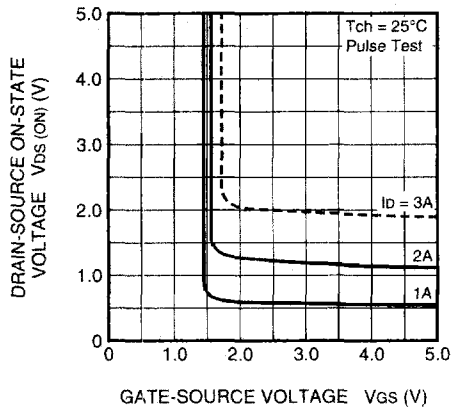
Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	150	V
V_{GS}	Gate-source voltage	$V_{DS} = 0V$	± 10	V
I_D	Drain current		2	A
I_{DM}	Drain current (Pulsed)		8	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 100\mu H$	2	A
I_S	Source current		2	A
I_{SM}	Source current (Pulsed)		8	A
P_D	Maximum power dissipation		20	W
T_{ch}	Channel temperature		$-55 \sim +150$	$^\circ\text{C}$
T_{stg}	Storage temperature		$-55 \sim +150$	$^\circ\text{C}$
—	Weight	Typical value	0.26	g

ELECTRICAL CHARACTERISTICS ($T_{ch} = 25^{\circ}\text{C}$)

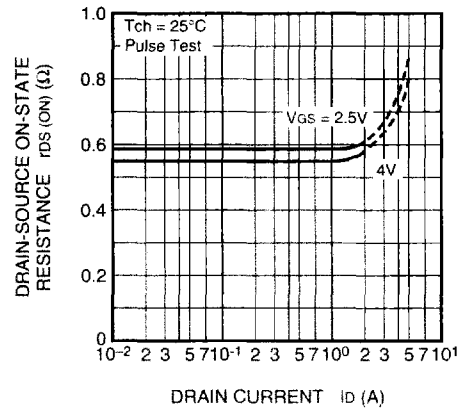
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$, $V_{DS} = 0\text{V}$	150	—	—	V
I_{GSS}	Gate leakage current	$V_{GS} = \pm 10\text{V}$, $V_{DS} = 0\text{V}$	—	—	± 0.1	μA
I_{DSS}	Drain current	$V_{DS} = 150\text{V}$, $V_{GS} = 0\text{V}$	—	—	0.1	mA
$V_{GS(th)}$	Gate-source threshold voltage	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	0.6	0.9	1.2	V
$r_{DS(on)}$	Drain-source on-state resistance	$I_D = 1\text{A}$, $V_{GS} = 4\text{V}$	—	0.58	0.75	Ω
$r_{DS(on)}$	Drain-source on-state resistance	$I_D = 1\text{A}$, $V_{GS} = 2.5\text{V}$	—	0.59	0.79	Ω
$V_{DS(on)}$	Drain-source on-state voltage	$I_D = 1\text{A}$, $V_{GS} = 4\text{V}$	—	0.58	0.75	V
$ y_{fs} $	Forward transfer admittance	$I_D = 1\text{A}$, $V_{DS} = 5\text{V}$	—	6.5	—	S
C_{iss}	Input capacitance	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	—	540	—	pF
C_{oss}	Output capacitance		—	60	—	pF
C_{rss}	Reverse transfer capacitance		—	15	—	pF
$t_{d(on)}$	Turn-on delay time		—	12	—	ns
t_r	Rise time	$V_{DD} = 80\text{V}$, $I_D = 1\text{A}$, $V_{GS} = 4\text{V}$, $R_{GEN} = R_{GS} = 50\Omega$	—	15	—	ns
$t_{d(off)}$	Turn-off delay time		—	45	—	ns
t_f	Fall time		—	27	—	ns
V_{SD}	Source-drain voltage	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$	—	1.0	1.5	V
$R_{th(ch-c)}$	Thermal resistance	Channel to case	—	—	6.25	$^{\circ}\text{C/W}$
t_{rr}	Reverse recovery time	$I_S = 2\text{A}$, $di/dt = -100\text{A}/\mu\text{s}$	—	65	—	ns

PERFORMANCE CURVES

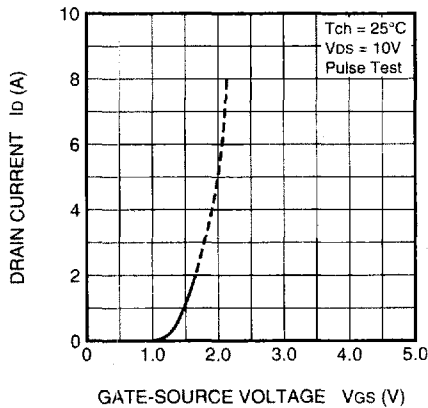
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



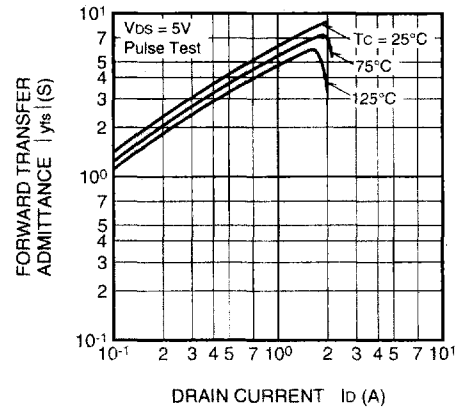
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



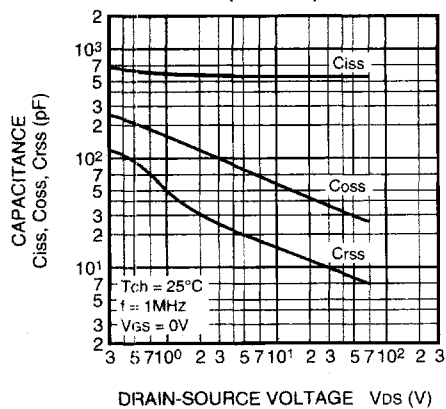
TRANSFER CHARACTERISTICS
(TYPICAL)



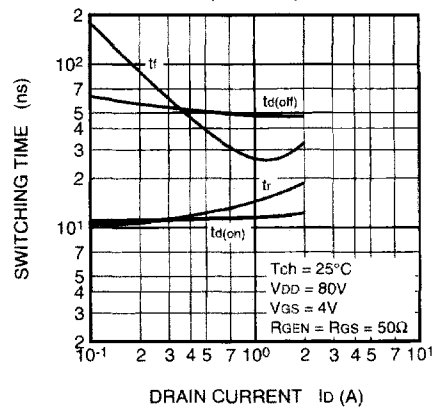
FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)



CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)



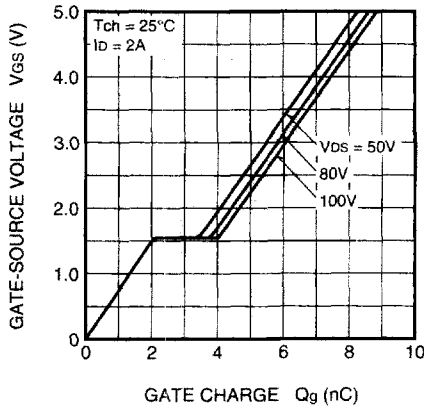
SWITCHING CHARACTERISTICS
(TYPICAL)



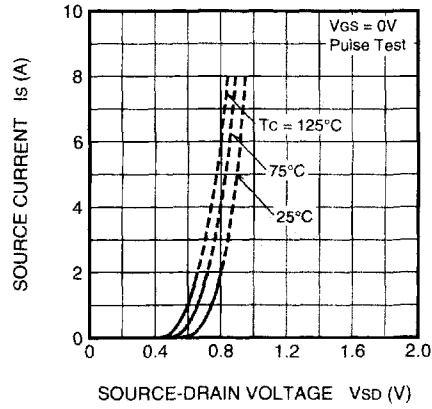
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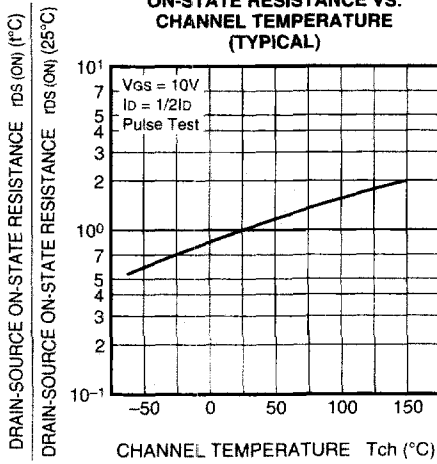
**GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)**



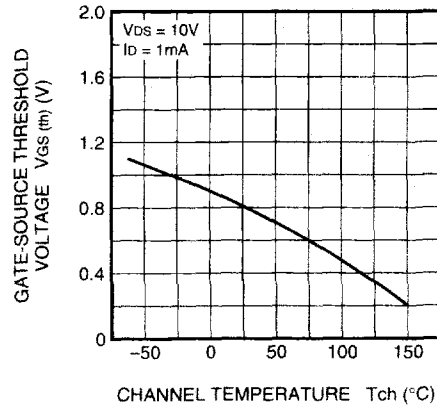
**SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



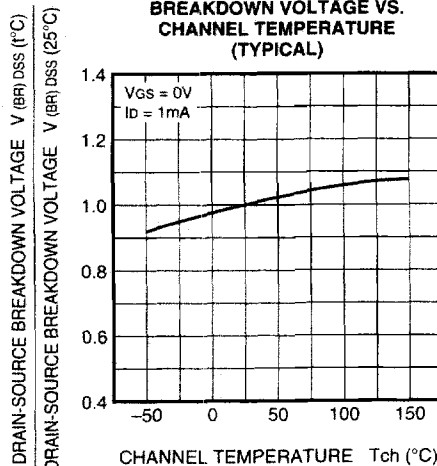
**ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**

